



# **Joint DoD/DOE Munitions Program (JMP)**

## **Five Year Plan**

**MEMS Reliability Task under  
Materials Reliability Project (TCG XIV)**



# Project '*Materials Reliability*'

## Five Year Plan for FY08-12

### ***MEMS Reliability Task***

Performing Organization: Sandia National Laboratories

Principal Investigator: Thomas Buchheit  
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Sandia National Laboratories  
Albuquerque, NM 87185

#### Key Customers:

Customer	Collaboration
<u>Picatinny Arsenal</u> <u>(Army Corrosion Office)</u> <i>Jim Zunino, Don Skelton,</i> <i>Robert Kuper, Frank Gagliardi</i>	<i>Develop MEMS Reliability Test Platform/Methods useful for the qualification of processing technologies for replacement SnA devices, IMU devices, and other MEMS-based RF devices.</i>
<u>Redstone Arsenal (AMRDEC)</u> <i>Abdul Kudiya</i> <i>Dave Locker</i>	<i>Post-Mortem characterization of prospective replacement MEMS devices.</i>
<u>NSWC</u> <i>Mike Bucher,</i> <i>Michael Deeds</i>	



# MEMS Reliability - Key Personnel

Name	Org	Role
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<b>Danelle Tanner</b> <a href="mailto:tannerdm@sandia.gov"><u>tannerdm@sandia.gov</u></a> (505)-844-8973	<b>Dept. 1769-1</b> <b>Sandia Labs</b>	<b>Reliability Physics</b>
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# Predictive Materials Aging and Reliability

## MEMS Reliability GOTChA Chart 5yr. plan



### Goal

Understand and predict the aging and reliability of MEMS materials

### Objectives

- Design, fabricate and characterize test structures to measure *process diagnostics*, strength, friction and fatigue response in various MEMS processing technologies
- Use test structures and post mortem characterizations to develop mechanism-properties relationships
- Design and perform series of experiments which isolate the effects of aging and environment on the performance of MEMS materials

### Challenges

- Test structures have only been developed in surface micromachined polysilicon and LIGA
- To establish mechanism-properties relationships in any materials/device class requires careful science-based research
- Mechanism-properties relationships must be linked to design and reliability of MEMS devices
- No current program exists for translating results into DOD/DOE device design optimization

### Approach

- Choose SOI as MEMS processing technology (relevant to DOD/DOE missions)
- Invest 1 ½ years to develop key mechanism-properties relationships in SOI, including submission of refined test geometry designs
- **Fabricate test structures in 2<sup>nd</sup>, preferably metal-based, MEMS processing technology**
- **Develop key mechanism-properties relationships in 2<sup>nd</sup> processing technology.**
- Use DOD input, previously developed test structures and fundamental knowledge gained from mechanism-properties studies to guide direction of aging and environment studies.



# Predictive Materials Aging and Reliability

## MEMS reliability- Funding- 5 yr. plan



### Planned:

FY08	FY09	FY10	FY11	
\$210K	\$210K	\$210K	\$220K	

### Historical:

FY03	FY04	FY05	FY06	FY07
\$0K	\$0K	\$0K	\$200K	\$200K

Includes the total of both DoD and DOE \$s



# Task 'MEMS Reliability' Four-Question Chart



## What are you trying to do in this task? *Understand the reliability MEMS materials and devices*

- Provide semi-standard measurement techniques, materials and tribological properties data within a MEMS fabrication processes
- Apply results and analysis to lifetime/reliability issues in prospective MEMS devices across the DOD/DOE complex

## What makes you think you can do it?

- Previously developed strength, friction and fatigue test designs for SMM polysilicon (one MEMS technology) will guide aging/lifetime/reliability diagnostic studies
- Experience with microsystems reliability physics

## What difference will it make?

- Optimized design and reliability of MEMS-based components and systems
- Properties database of MEMS process materials
- Mechanism-based understanding of reliability and lifetime issues associated with MEMS devices

## What / When Will You Deliver?

- SOI strength, friction, fatigue test structure fabrication and preliminary evaluation 10/06
- Demonstrated ability to drop-in to a second MEMS processing technology by 09/08
- Preliminary lifetime-reliability study using SOI diagnostic test structures 1/08



# Predictive Materials Aging and Reliability

## MEMS Reliability FY07 specific activities



- Finish 700  $\mu\text{m}$  deflection experiments on mass-spring structures
- Begin Testing **in-plane** and out-of-plane fatigue diagnostic structures
- Characterize and begin baseline testing friction test structures
  - (8 die – levitation forces range of friction forces, test with monolayer coatings)

Later FY2007 deliverables:

- Second SOI die design
- Accelerated aging study



# Predictive Materials Aging & Reliability (MEMS)





# Summary of Kickoff meeting

## MEMS Reliability Task subgroup



Two categories of Reliability issues:

- Initial Design/Processing
- Aging/Lifetime/Storage

Two categories Devices:

- Homegrown
- COTS-commercial

Fault Tree items:

- Shock-** Pyroshock, High G shock
- Outgassing** – Degradation of packaging seal and hermeticity issues
- Storage environments** -Long term storage issues, e.g. temp. cycling
- Interacting Surfaces**- Adhesion of devices (stiction), metal film delamination within devices

- Current project direction is a bottom-up approach, developing diagnostics to gain a fundamental understanding of the process dependent key characteristics of MEMS materials.
- Some funding will be redirected to a top-down approach, i.e device failure determination. Isolating primary causes of failure in prospective DOD MEMS devices will feed into the bottom-up approach, developing diagnostics to isolate key failure and reliability mechanisms

Deliverable: Accelerated Aging protocol leading to a specification for the qualification of MEMS devices for military applications



# List of DOD MEMS Devices

Class I – no moving parts

Class II – moving parts with no contact

Class III – moving with impacting surfaces

Class IV – moving with rubbing surfaces

S&A for the XM29 Airburst Weapon. The technology here is a Ni on steel that is etched to make the structures (kind of LIGA-like). The device is not hermetically sealed but will be sealed in the overall fuze component.

IMU (Inertial Measurement Unit) for common guidance. This is SOI technology being developed by Honeywell.

ARL RF Switch. Manufactured by Harry Diamond Labs- it has undergone some environmental stress testing.

NSWC S&A. basic geometry platform for several systems



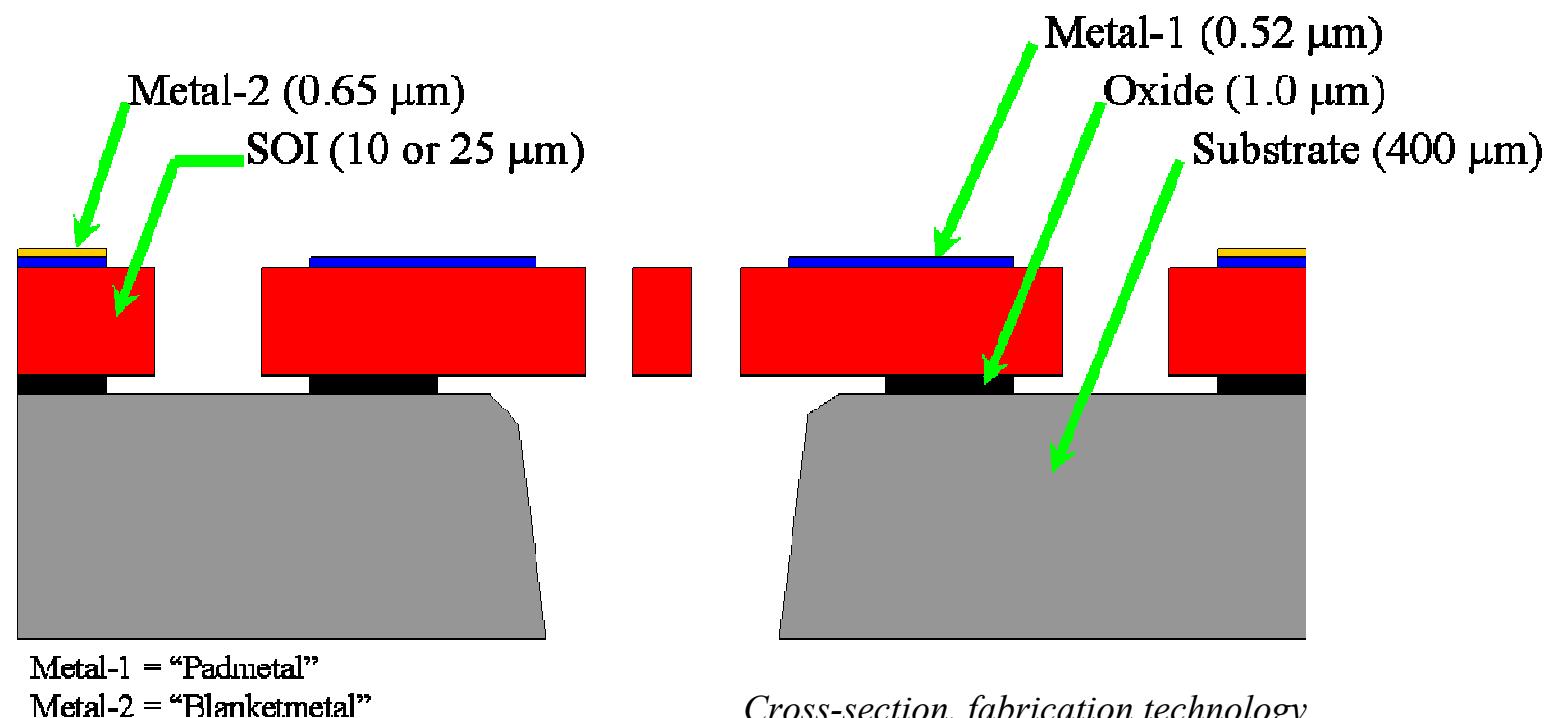
# MEMSCAP SOI-MUMPS fabrication process

*process used for test structure fabrication under MEMS Reliability MOU*



Online at: [www.memsrus.com](http://www.memsrus.com)

- 1 structural layer located on 1 handle wafer
- (15) dice, 9x9 mm
- Handle wafer: <001>, 400  $\mu\text{m}$  thick, P-doped @ 1-10 Ohm-cm
- Oxide: thermal
- Structural layer: <110> along x- and y-axes. <001> is 45°. P-doped at top surface.
- More info available in wafer data sheet, design rules document



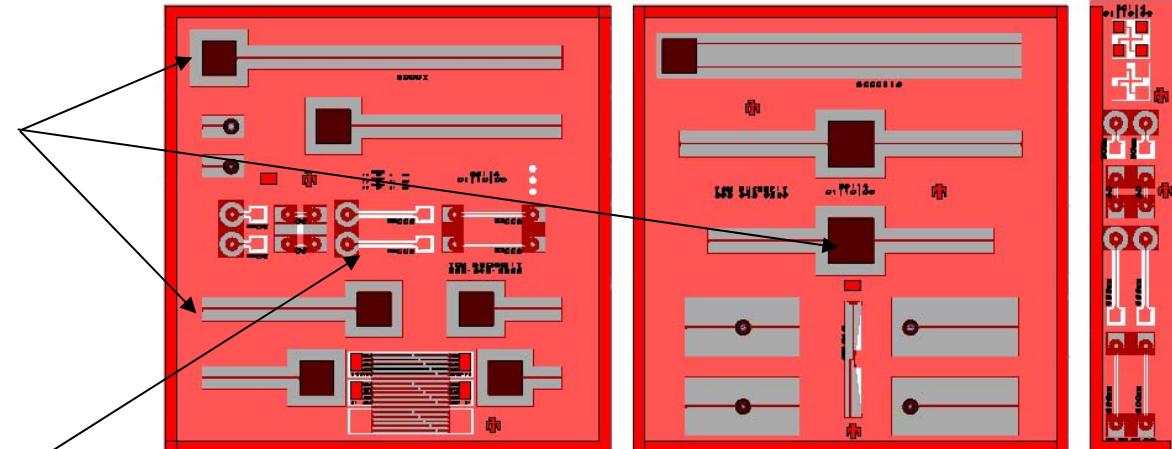
*Cross-section, fabrication technology*



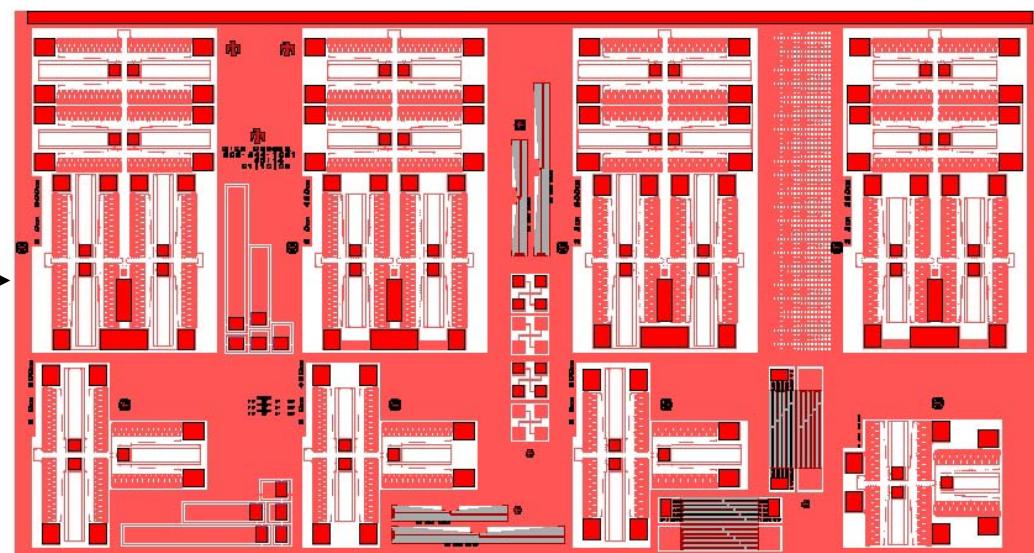
# 1<sup>st</sup> generation SOI design containing strength, fatigue and friction test structures



Fatigue test structures



strength test structures

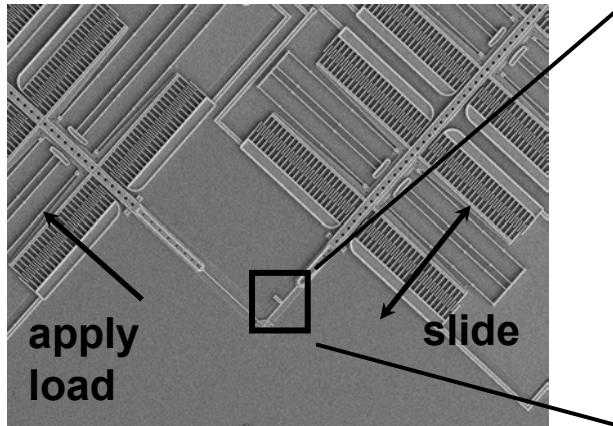


friction and wear test structures

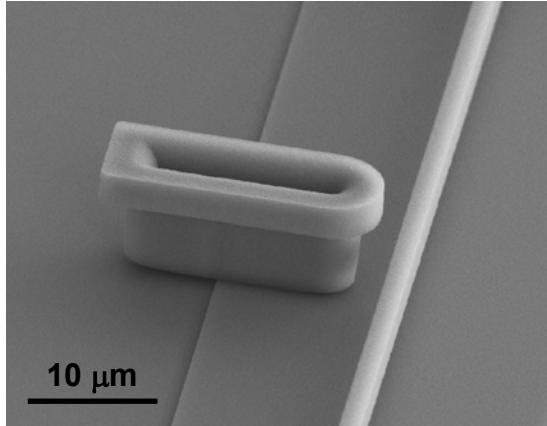




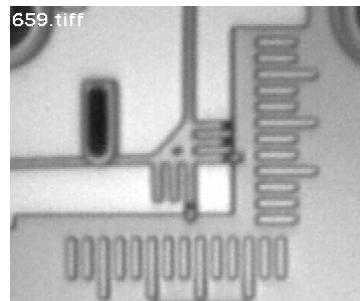
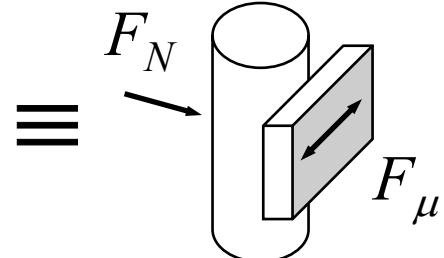
# MEMS Tribometer used to measure friction



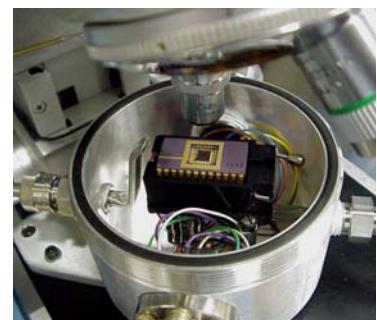
D.C. Senft and M.T. Dugger, Proc. SPIE, 3224 (1997) pp. 31-38.



**“Surface Micromachined Sidewall Tribometer”**



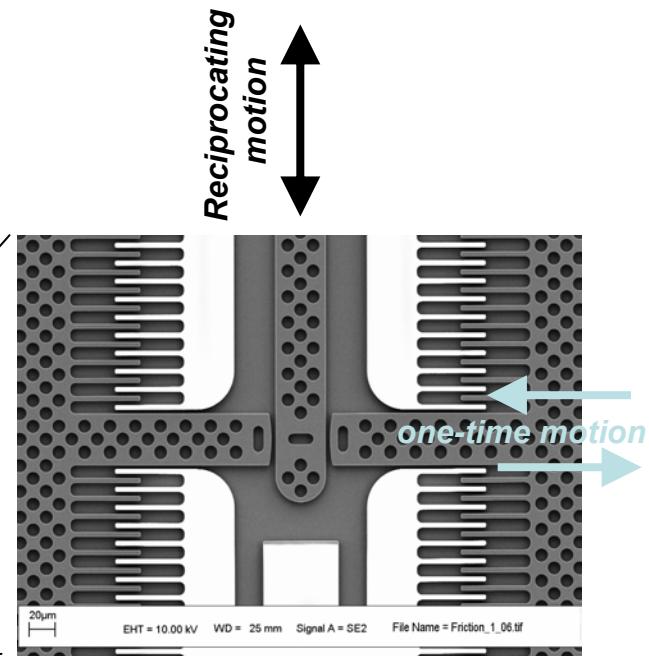
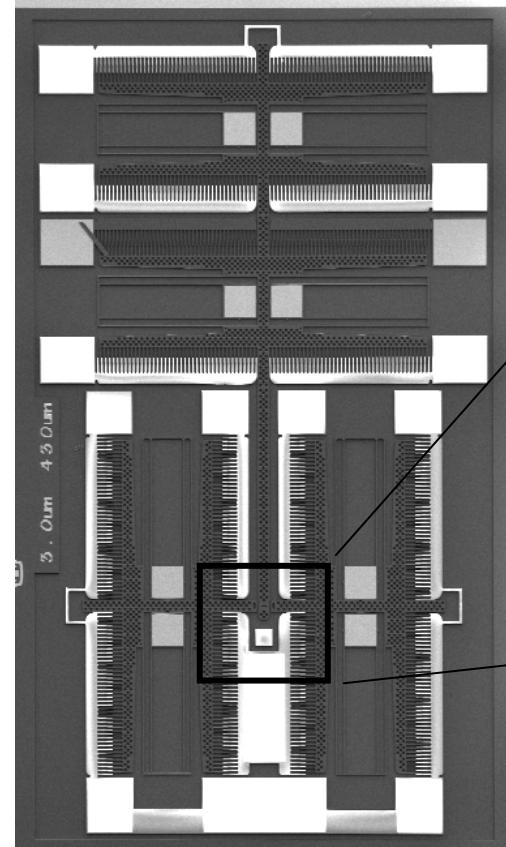
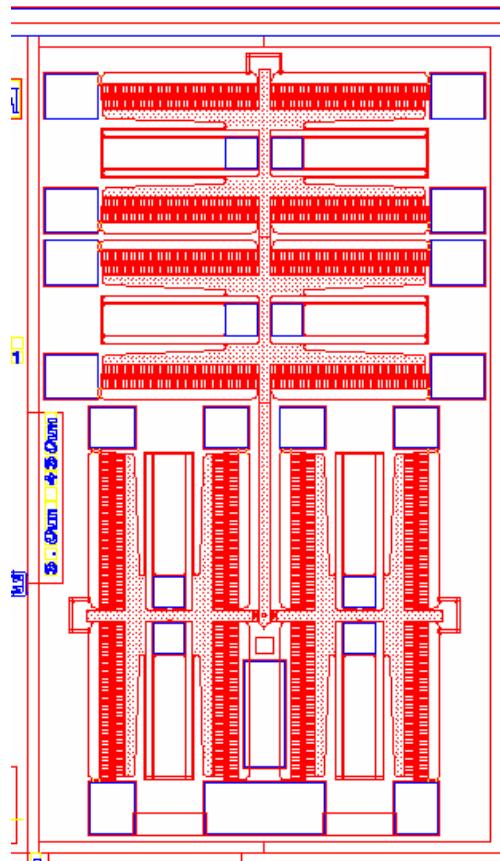
environmental cell for packaged devices



- **Static Friction**
  - beam is pulled into contact with post
  - lateral voltage (force) is ramped up until beam slips laterally
- **Dynamic Friction**
  - beam is pulled into contact with post
  - beam is oscillated laterally against post
- **Pull-Off Force**
  - beam is pulled into contact with post
  - normal voltage (force) decreased until beam pulls off of post

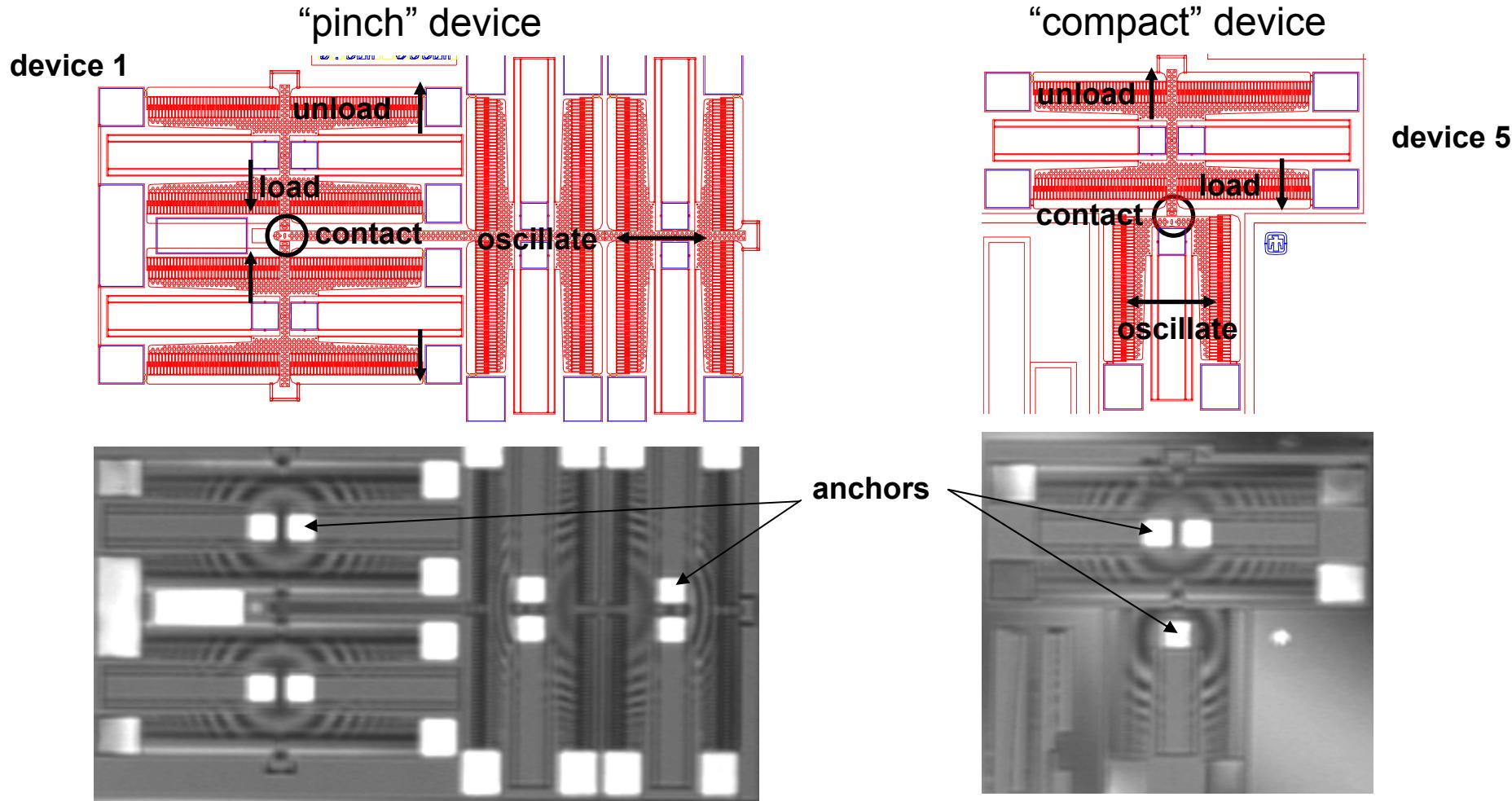


# A SOI fabricated Friction and Wear device





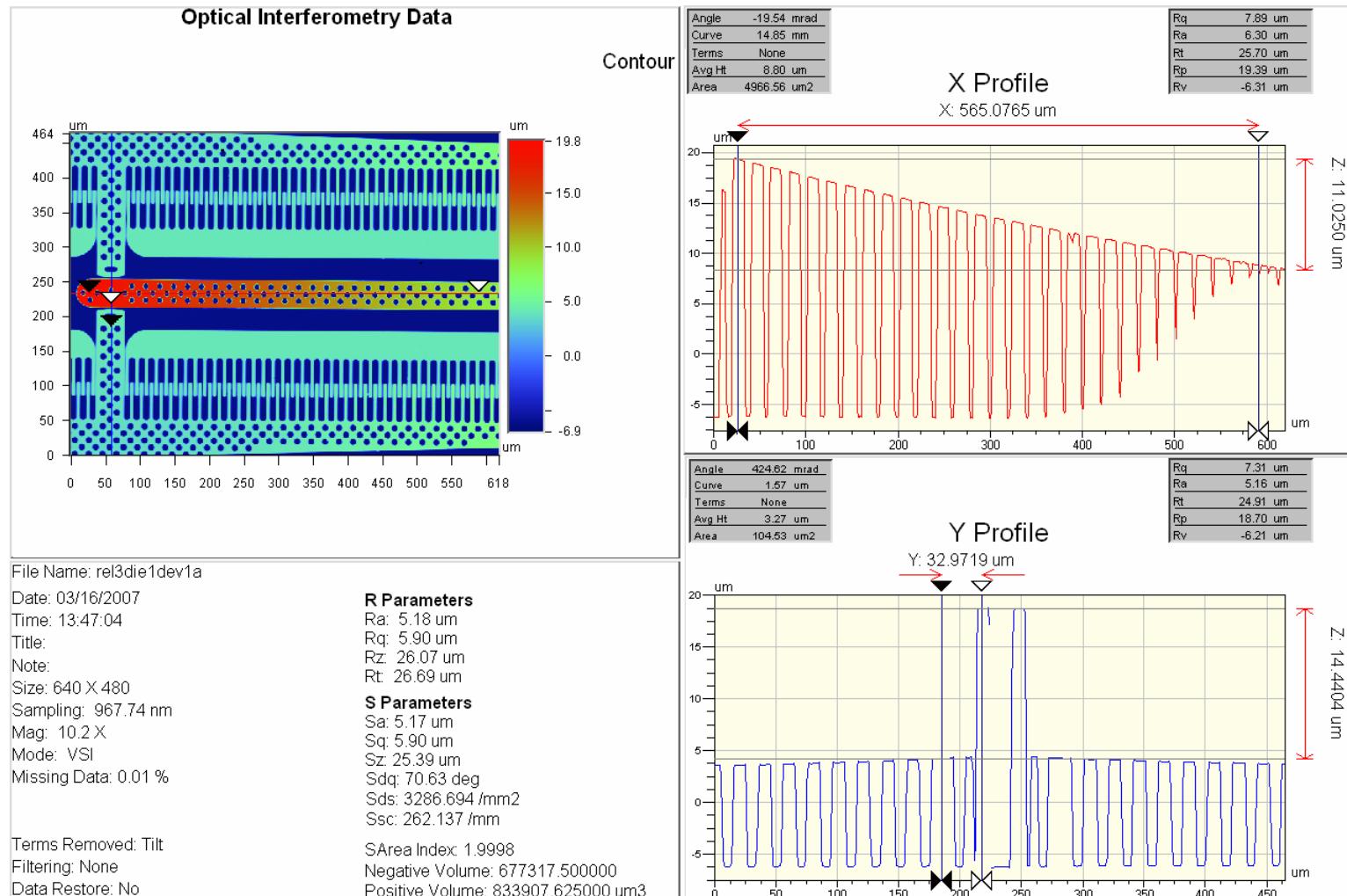
# Stress observed in 1<sup>st</sup> generation SOI tribometer



- Suspended structures curled out of plane away from anchors



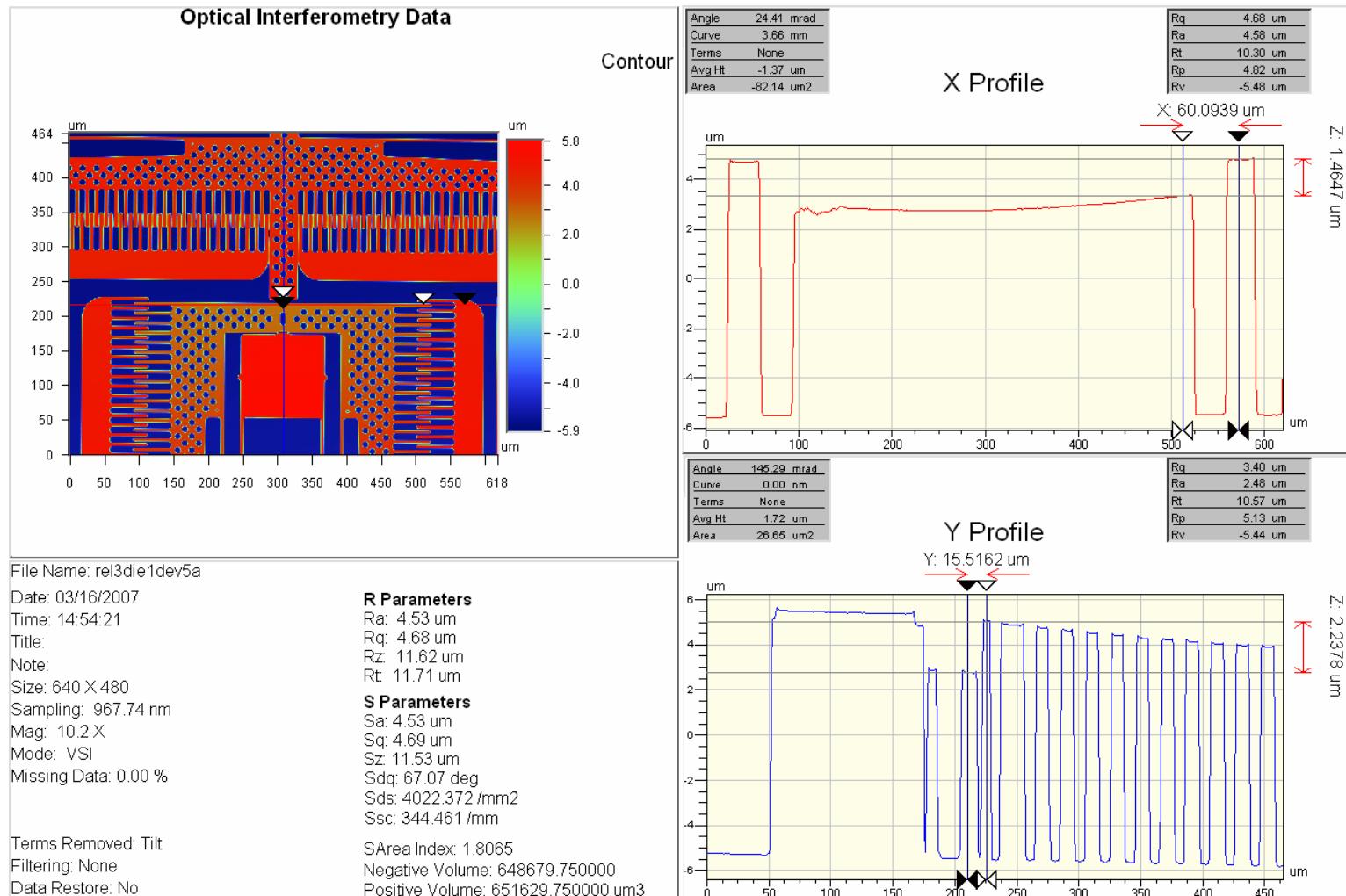
# Misalignment of mechanical contact



- Pinch actuators do not contact oscillating beam



# Compact device exhibits less misalignment of mechanical contacts



- Contacts will still touch over > 7.5  $\mu\text{m}$  of their height



# Lessons learned in SOI friction devices

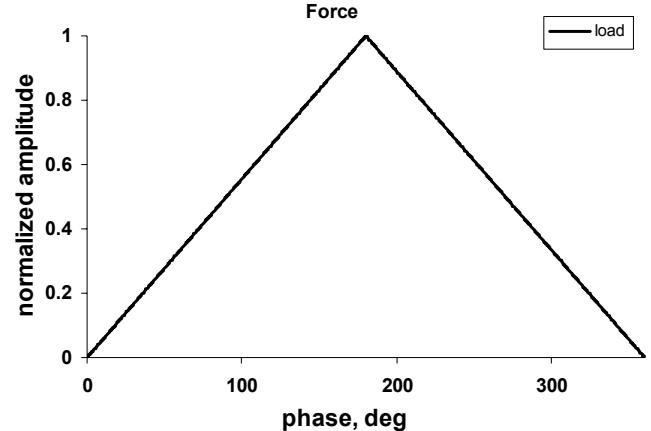
- Stress in structural layer higher than observed in (SUMMiT) polysilicon process
  - keep suspended structures as small as possible to ensure alignment
- Adhesion effects compounded by lack of dimples
  - smooth bottom surface of structural layer easily sticks down, even with hydrophobic coatings
  - DRIE under large structures, or use thicker sacox layer
- Small gold fields undercut during release
  - omit lettering to avoid “alphabet soup”



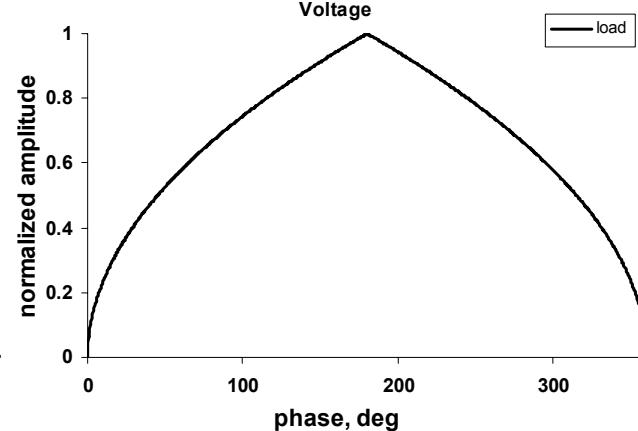
# Adhesion tests monitor changes in intrinsic force that adds to normal load



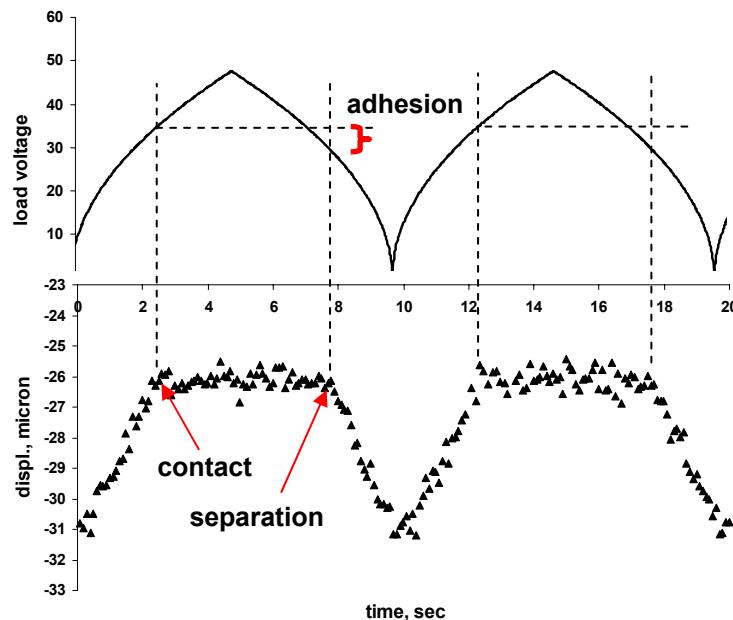
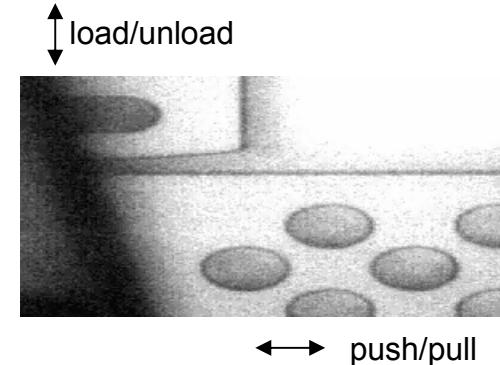
desired displacement



required input



resulting motion



**(contact - separation) voltage permits quantification of adhesion force**

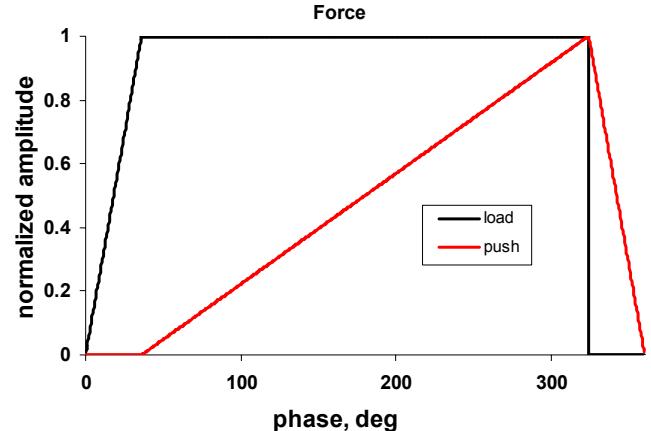
- measure after operation, environment exposure, aging, etc.
- examine changes in contact surfaces due to degradation



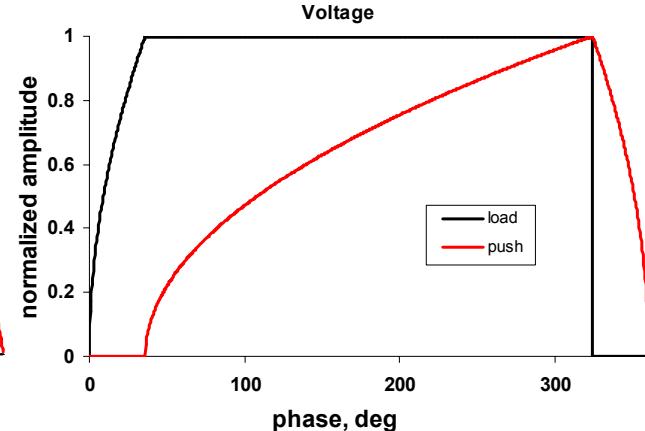
# Static friction test is used to determine changes in start-up force for sliding surfaces



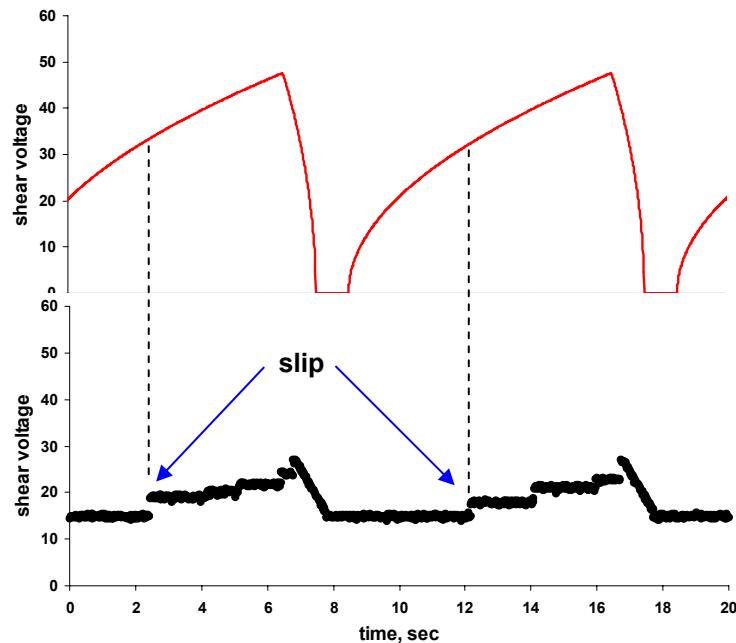
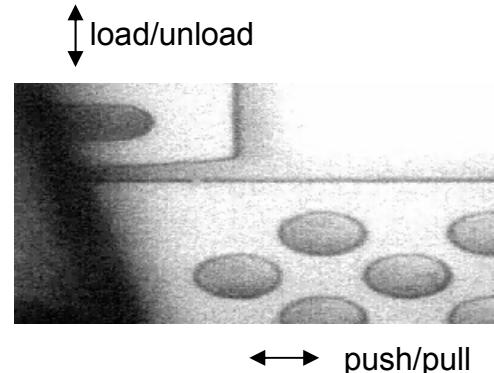
desired displacement



required input



resulting motion



**voltage at slip permits quantification of static friction force**

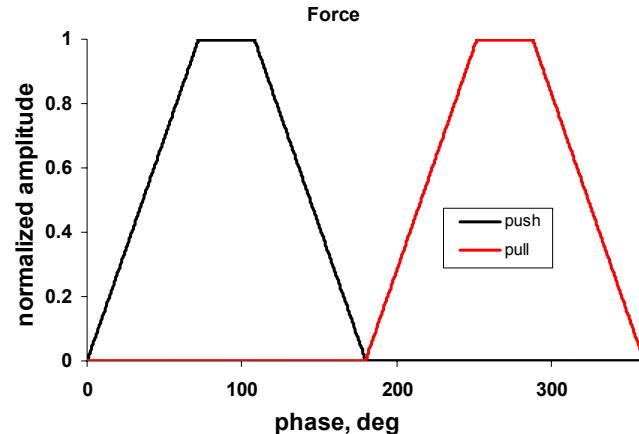
- measure after operation, environment exposure, aging, etc.
- examine changes in contact surfaces due to degradation



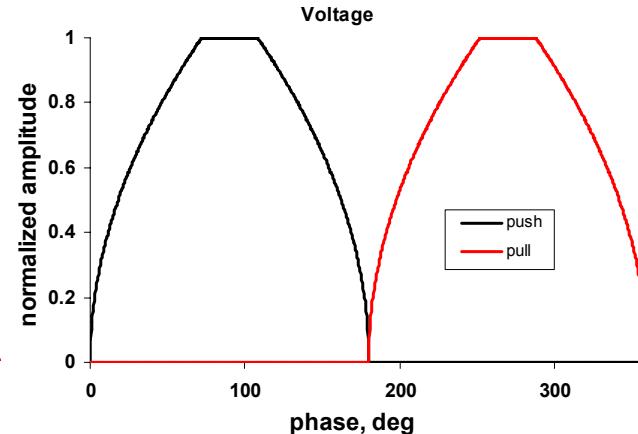
# Dynamic friction test is used to investigate surface degradation during shear



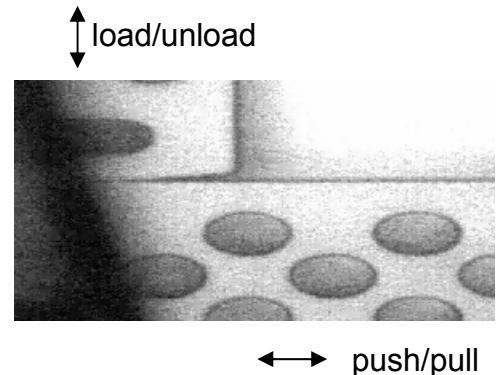
desired displacement



required input



resulting motion

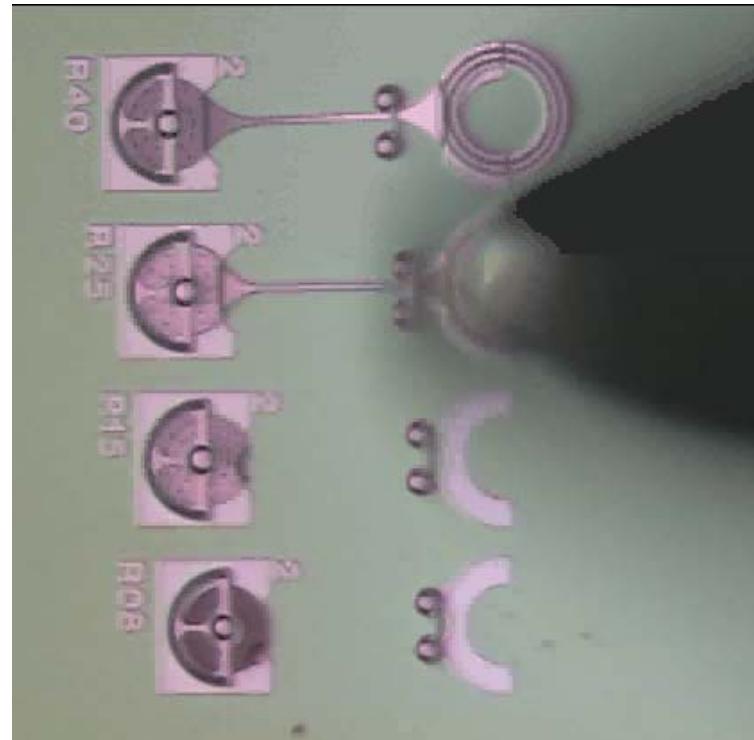
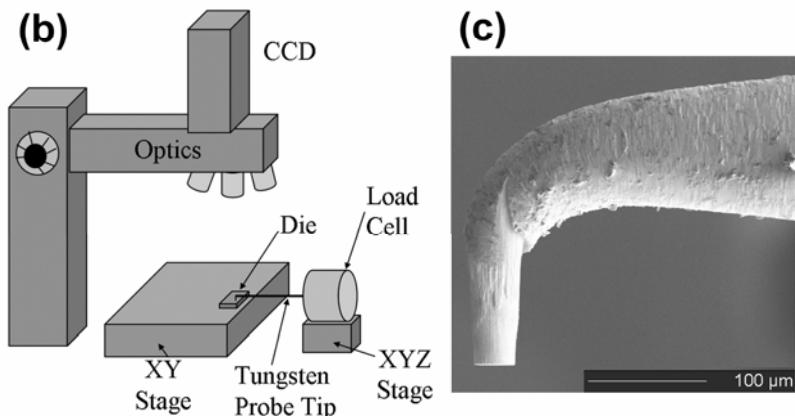
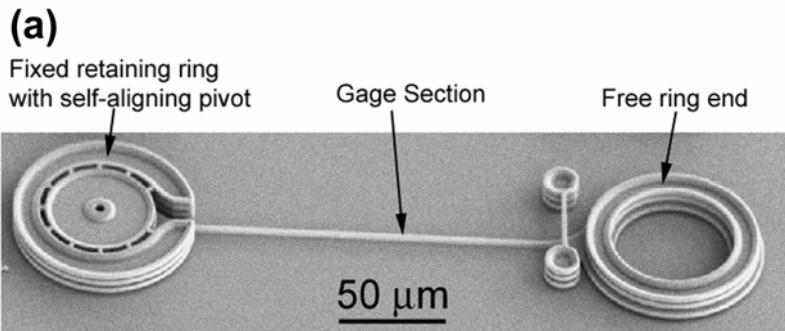


displacement amplitude is related to dynamic friction force

- $F_d = k\Delta x$ , where  $k$  = suspension stiffness and  $\Delta x$  is reduction in device amplitude from non-contact
- examine changes in contact surfaces due to degradation

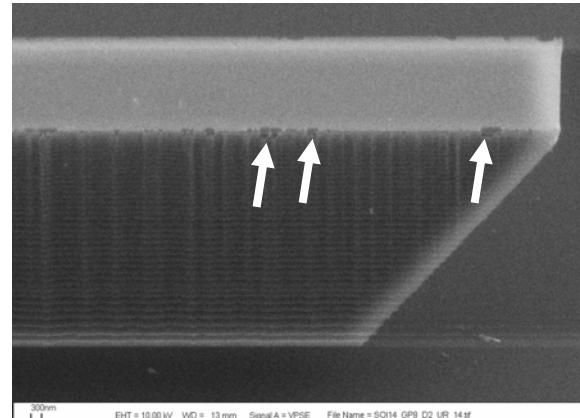
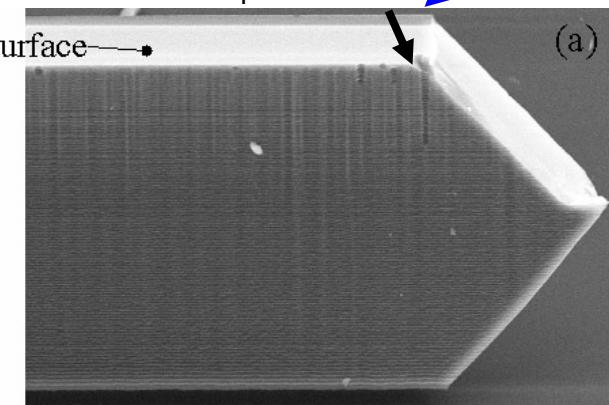
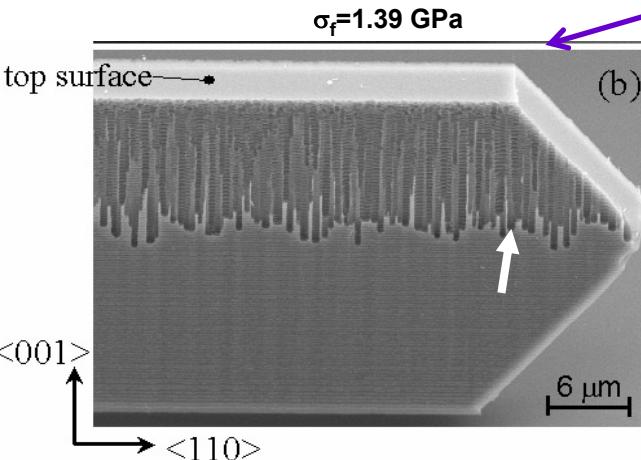
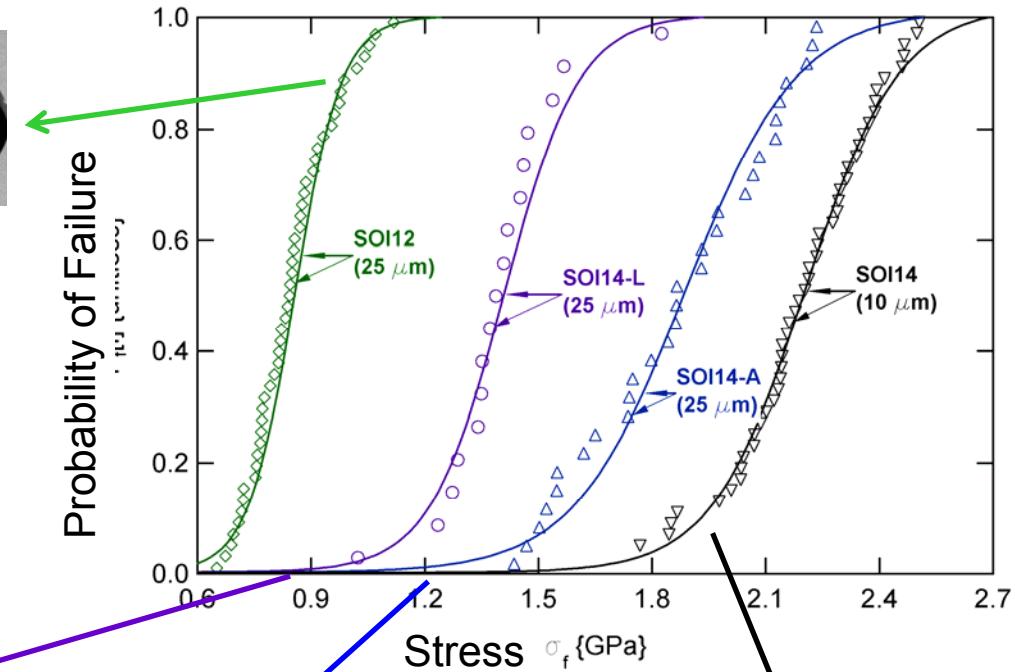
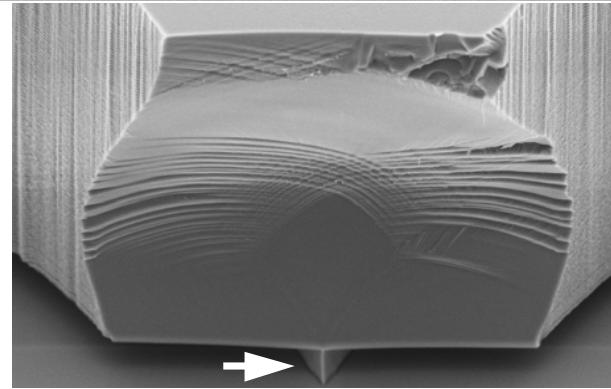
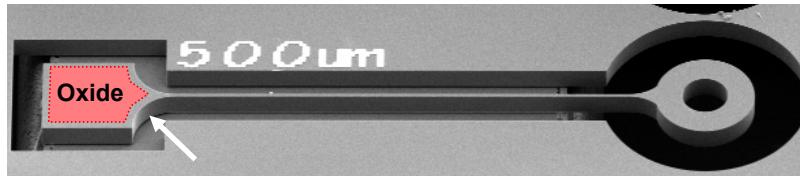


# Fundamental Strength Measurements On Microfabricated Silicon



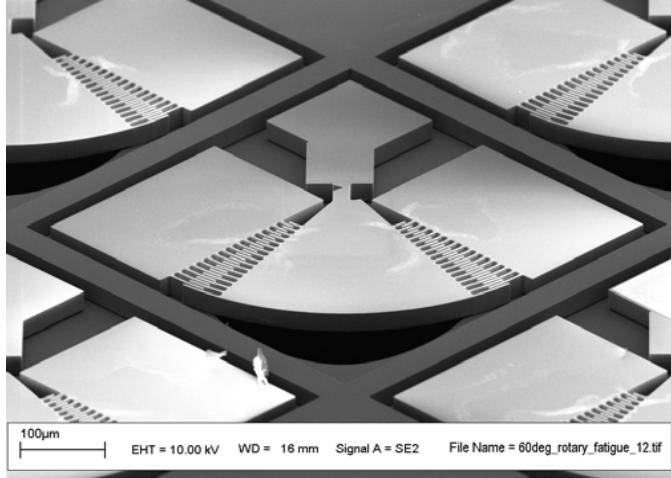


# Surface Roughness and Processing induced flaws govern fracture behavior in SOI

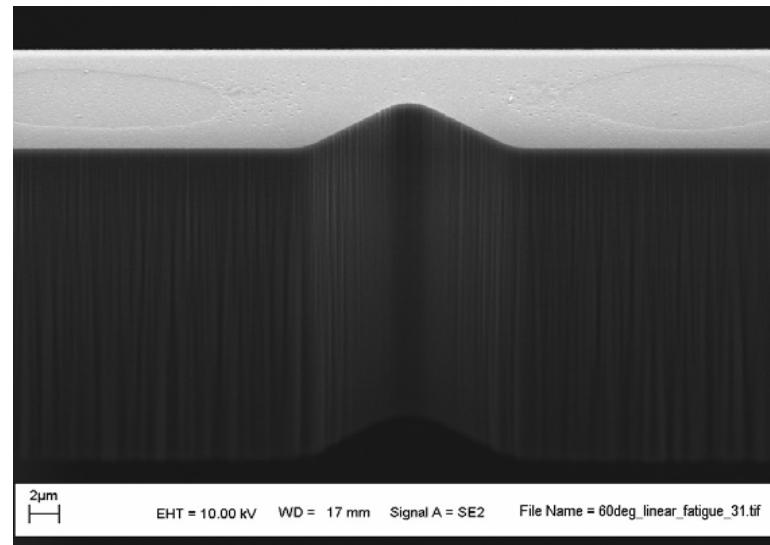
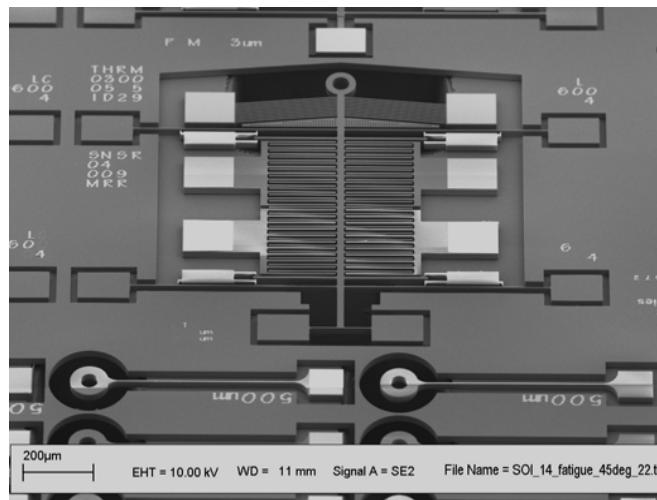




# In-Plane fatigue test structures



- Devices actuated at 100 Hz (thermal “resonance” at 200 Hz)
- Test rate: 8.6 million cycles/day

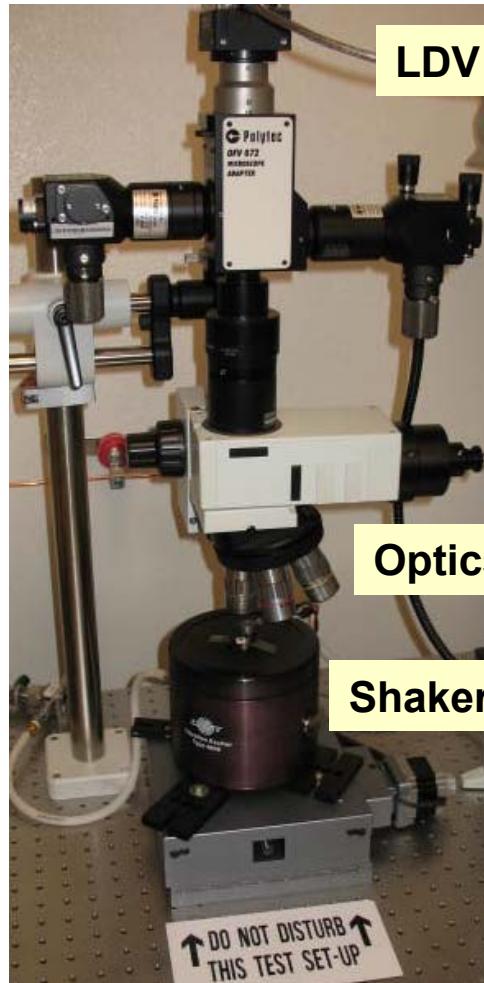




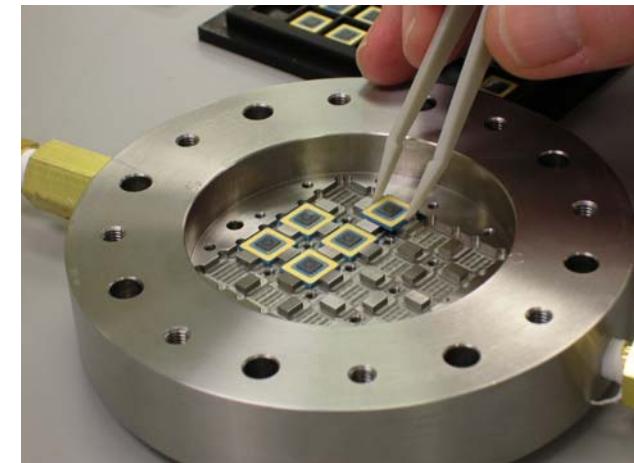
# Long Term Reliability MEMS test-bed

used to performed  $\pm 80 \mu\text{m}$  and  $\pm 700 \mu\text{m}$  fatigue experiments on mass-spring test structure

## Experimental set-up



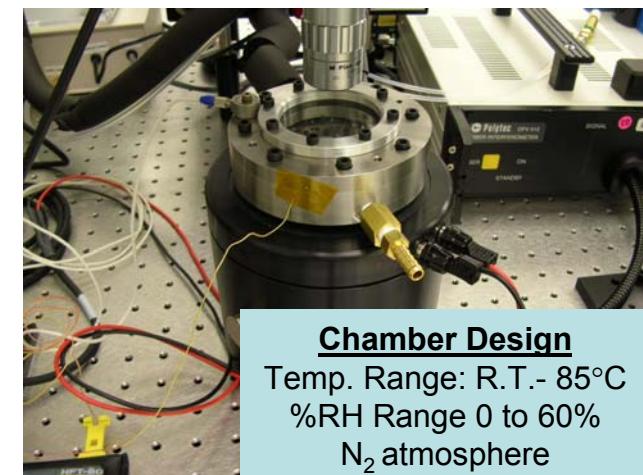
## Environmental Control Chamber



## Accelerometer for additional sensing



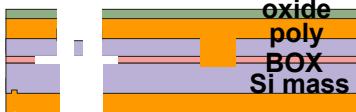
- Environmental control chamber used for  $\pm 80 \mu\text{m}$  experiments
- Accelerometer used for  $\pm 700 \mu\text{m}$  experiments



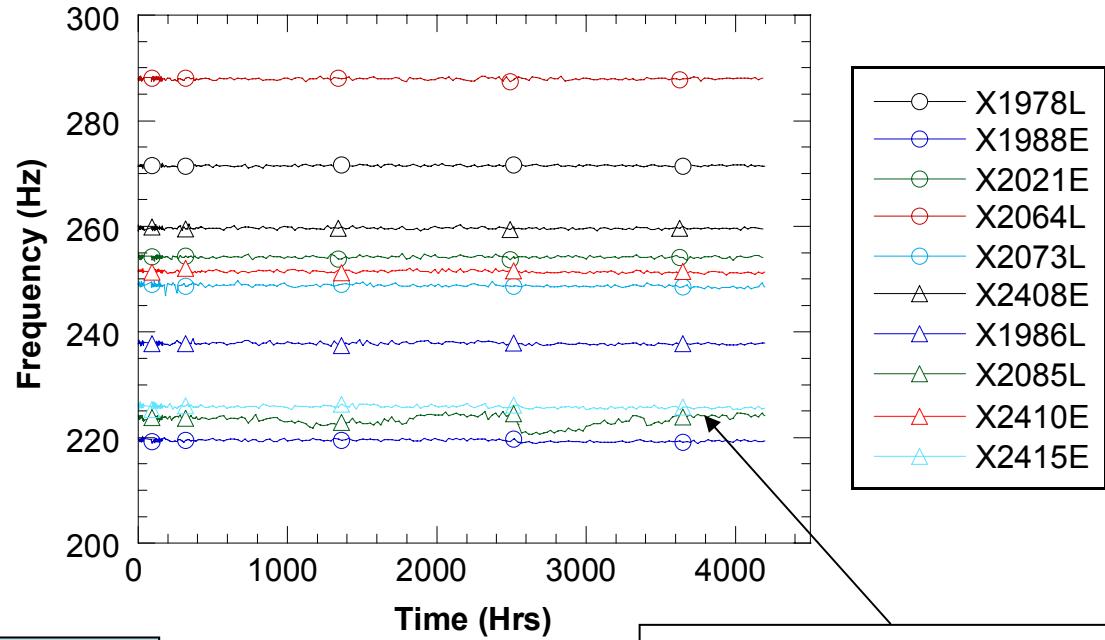
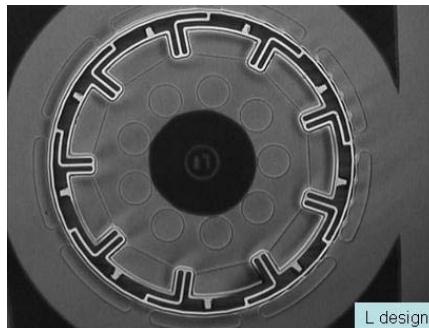
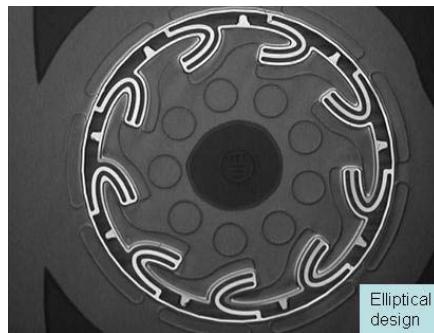


# A long-term fatigue reliability study on the spring-mass test structure

## Resonant Frequency Tracking of 10 SOI-spring-mass structures



A different SOI process was used to fabricate these structures



250 Hz for 4000hrs =  
3.6 billion cycles

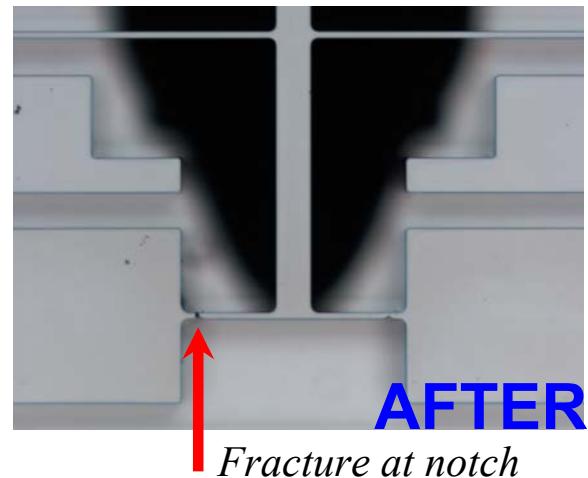
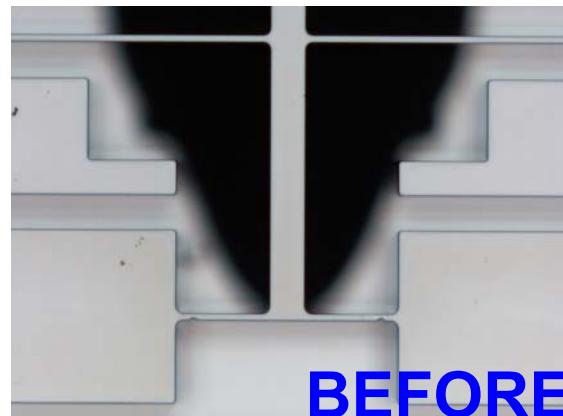
Broken spring noted on X2085L  
before fatigue testing experiment

- Spring-mass devices exhibited no evidence of fatigue when cycled at its designed operational range of  $\pm 80 \mu\text{m}$ .
- Device-to-device variation of resonant frequency was observed.



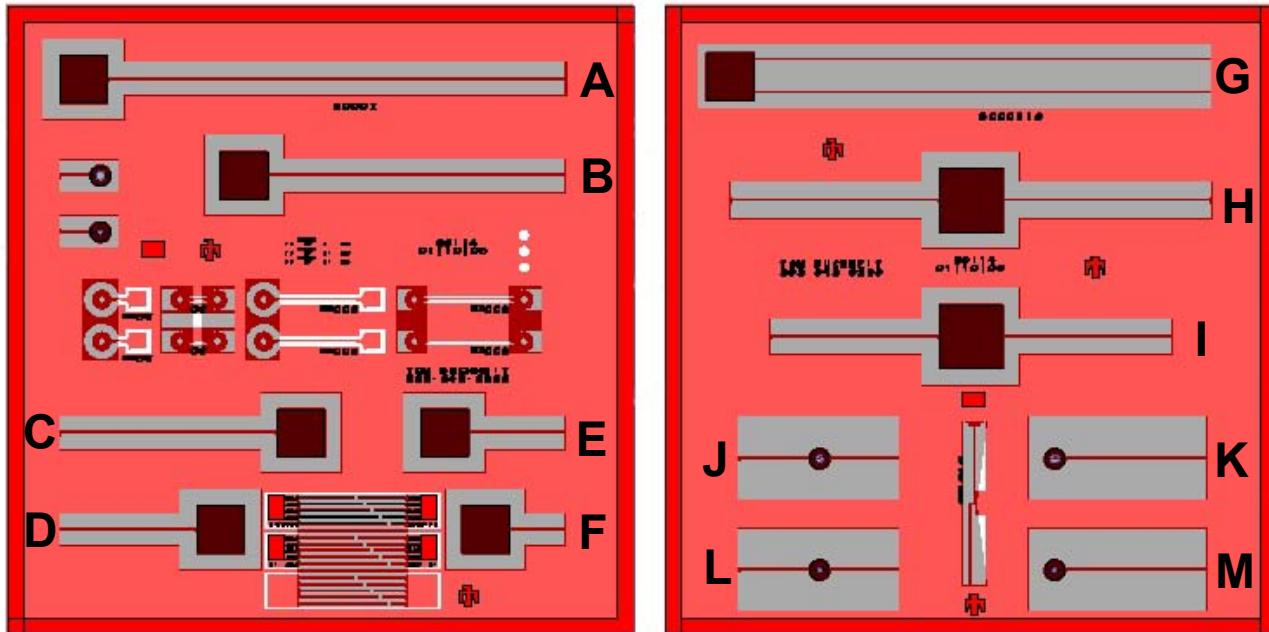
# In-Plane Fatigue Response of MEMSCAP SOI

DIE	Specimen ID	Applied Voltage	Cycles to Failure ( $\times 10^6$ )	
SOI 14 GP5 D1	ID 18	9	37.89	
SOI 14 GP3 D3	ID 28	10	25.47	
SOI 14 GP4 D2	ID 16	10	32.4	
SOI 14 GP4 D2	ID 18	10.5	32.4	
SOI 14 GP4 D1	ID 28	12	27	
SOI 14 GP5 D1	ID 28	12.5	25.92	
SOI 14 GP5 D2	ID 16	10	23.4	
SOI 14 GP5 D2	ID 28	10.5	3.24	
SOI 14 GP5 D5	ID 20	13	32.4	
SOI 14 GP5 D5	ID 28	12.5	3.06	





# Out-of-plane fatigue response in MEMSCAP SOI

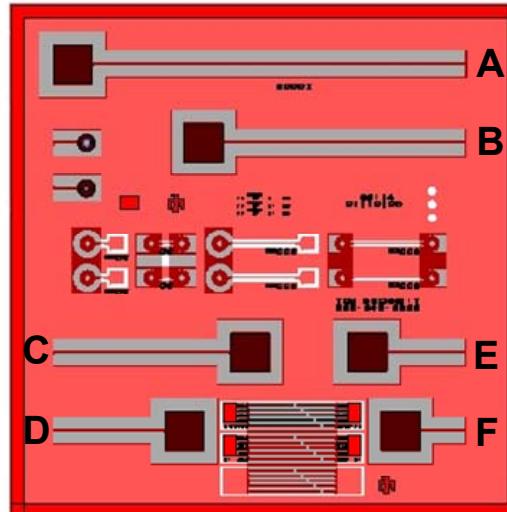


Label	Length (μm)	Label	Length (μm)	Label	Length (μm)
A	3000	D	1000	G	3000
B	2000	E	750	H	3000
C	1500	F	500	I	2500



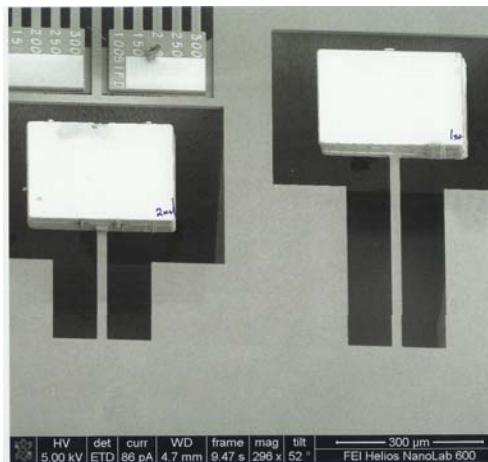
# Out-of-plane fatigue response in MEMSCAP SOI

- Failure of test structures did not occur during the initial stage of testing



Beam	$f_n$ (hz)	10g Accel.	max. stress	20g Accel.	max. stress
A	<i>did not fabricate</i>				
B	695	180 $\mu\text{m}$		380 $\mu\text{m}$	371 MPa
C	1050	93 $\mu\text{m}$		180 $\mu\text{m}$	312 MPa
D	1910	52 $\mu\text{m}$		104 $\mu\text{m}$	406 MPa
E	3000	36 $\mu\text{m}$		67 $\mu\text{m}$	465 MPa
F	5460	19 $\mu\text{m}$		36 $\mu\text{m}$	562 MPa

- Adding weight to out-of-plane fatigue structures increases the maximum stress at resonance



Beam	$f_n$ (hz)	$f_n$ (hz) FIB	$f_n$ (hz) Au-pre	20g Accel.	
B	695				
C	1050		323	800 $\mu\text{m}$	1.39 GPa
D	1910		570		
E	3000	1840		160 $\mu\text{m}$	1.11 GPa
F	5460				



# MEMS Reliability Task

## Outcomes/Accomplishments for FY07



- Finish 700  $\mu\text{m}$  deflection experiments on mass-spring structures
- Begin Testing **in-plane** and out-of-plane fatigue diagnostic structures
- Characterize and begin baseline testing friction test structures
  - (8 die – levitation forces range of friction forces, test with monolayer coatings)

Later FY2007 deliverables:

- Second SOI die design
- Accelerated aging study